# MOSFET – Power, Single, N-Channel

40 V, 0.67 mΩ, 370 A

# NTMFS5C404NL

#### **Features**

- Small Footprint (5x6 mm) for Compact Design
- Low R<sub>DS(on)</sub> to Minimize Conduction Losses
- Low Q<sub>G</sub> and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			$V_{DSS}$	40	V
Gate-to-Source Voltage			V <sub>GS</sub>	±20	V
Continuous Drain	T <sub>C</sub> = 25°C		I <sub>D</sub>	370	Α
Current R <sub>θJC</sub> (Notes 1, 3)	Steady	T <sub>C</sub> = 100°C		260	
Power Dissipation	State	T <sub>C</sub> = 25°C	$P_{D}$	167	W
R <sub>θJC</sub> (Note 1)		T <sub>C</sub> = 100°C		67	
Continuous Drain		T <sub>A</sub> = 25°C	I <sub>D</sub>	52	Α
Current R <sub>0JA</sub> (Notes 1, 2, 3)	Steady	T <sub>A</sub> = 100°C		37	
Power Dissipation	State	T <sub>A</sub> = 25°C	$P_{D}$	3.2	W
R <sub>θJA</sub> (Notes 1 & 2)		T <sub>A</sub> = 100°C		1.3	
Pulsed Drain Current	$T_A = 25$	°C, t <sub>p</sub> = 10 μs	I <sub>DM</sub>	900	Α
Operating Junction and Storage Temperature			T <sub>J</sub> , T <sub>stg</sub>	-55 to + 175	°C
Source Current (Body Diode)			I <sub>S</sub>	184	Α
Single Pulse Drain-to-Source Avalanche Energy (I <sub>L(pk)</sub> = 38 A)			E <sub>AS</sub>	907	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State	$R_{\theta JC}$	0.75	°C/W
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	39	

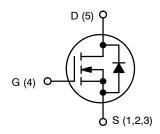
- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
- 2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
- 3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



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V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX
40 V	0.67 m $\Omega$ @ 10 V	070 4
40 V	1.0 mΩ @ 4.5 V	370 A

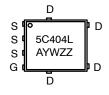


**N-CHANNEL MOSFET** 

#### MARKING DIAGRAM



DFN5 (SO-8FL) CASE 506EZ



5C404L = Specific Device Code A = Assembly Location

Y = Year
W = Work Week
ZZ = Lot Traceability

#### **ORDERING INFORMATION**

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise specified)

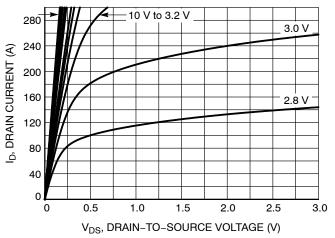
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	•						
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /				21.6		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	T <sub>J</sub> = 25 °C			10	
		V <sub>DS</sub> = 40 V	T <sub>J</sub> = 125°C			250	μΑ
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS}$	<sub>S</sub> = 20 V			100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = 250 \mu A$		1.2		2.0	V
Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>	·			-6.2		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 50 A		0.52	0.67	
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 50 A		0.75	1.0	mΩ
Forward Transconductance	9FS	V <sub>DS</sub> =15 V, I <sub>D</sub> = 50 A			270		S
CHARGES, CAPACITANCES & GATE RE	SISTANCE						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 25 V			12168		pF
Output Capacitance	C <sub>OSS</sub>				4538		
Reverse Transfer Capacitance	C <sub>RSS</sub>				79.8		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A			81		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A			181		1
Threshold Gate Charge	Q <sub>G(TH)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A			8.5		nC
Gate-to-Source Charge	$Q_{GS}$				27.8		
Gate-to-Drain Charge	$Q_{GD}$				23.8		
Plateau Voltage	$V_{GP}$				2.7		V
SWITCHING CHARACTERISTICS (Note 5	)						
Turn-On Delay Time	t <sub>d(ON)</sub>	$V_{GS}$ = 4.5 V, $V_{DS}$ = 20 V, $I_{D}$ = 50 A, $R_{G}$ = 1.0 $\Omega$			24		- ns
Rise Time	t <sub>r</sub>				135		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				87		
Fall Time	t <sub>f</sub>				157		
DRAIN-SOURCE DIODE CHARACTERIS	TICS						
Forward Diode Voltage	VGS	V <sub>GS</sub> = 0 V,	T <sub>J</sub> = 25°C		0.7	1.2	.,
		I <sub>S</sub> = 50 A	$I_{S} = 50 \text{ A}$ $T_{J} = 125^{\circ}\text{C}$		0.61		V
Reverse Recovery Time	t <sub>RR</sub>	$V_{GS} = 0 \text{ V, dIS/dt} = 100 \text{ A/}\mu\text{s,}$ $I_{S} = 50 \text{ A}$			97.4		
Charge Time	ta				46.5		ns
Discharge Time	t <sub>b</sub>				50.9		
Reverse Recovery Charge	Q <sub>RR</sub>				190		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width  $\leq 300~\mu s$ , duty cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures.

#### **TYPICAL CHARACTERISTICS**



800 700 ID, DRAIN CURRENT (A) 600 500 400 300  $T_J = 25^{\circ}C$ 200  $T_{J} = 125^{\circ}$ 100  $T_{.1} = -55^{\circ}C$ 0 0 0.5 2.0 3.0 3.5 1.0 1.5 2.5 V<sub>GS</sub>, GATE-TO-SOURCE VOLTAGE (V)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics

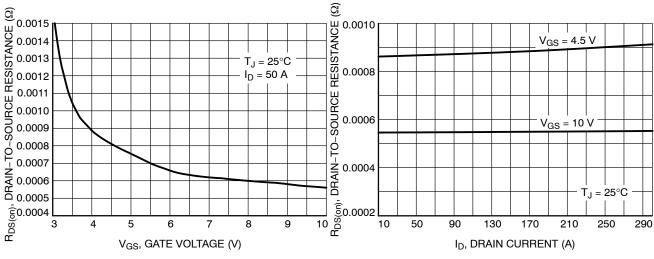
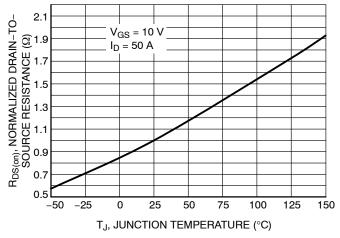


Figure 3. On-Resistance vs. Gate-to-Source Voltage

Figure 4. On-Resistance vs. Drain Current and Gate Voltage



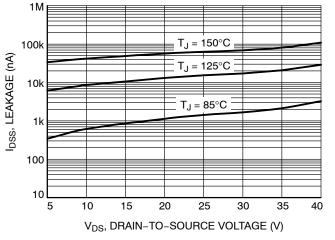
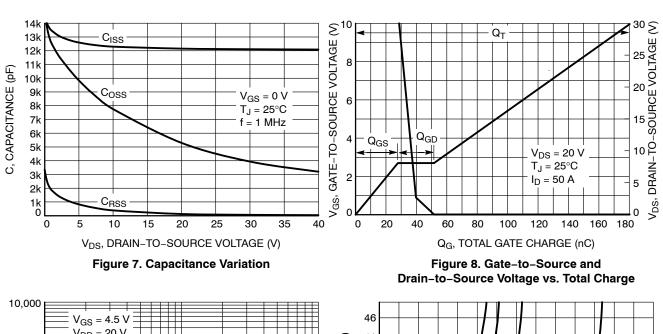
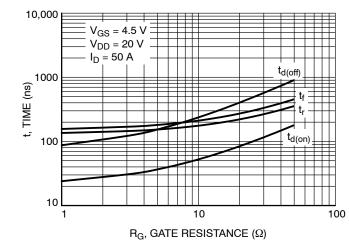


Figure 5. On–Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current vs. Voltage

#### **TYPICAL CHARACTERISTICS**







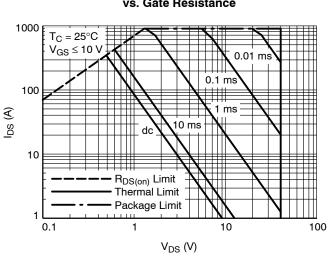


Figure 11. Safe Operating Area

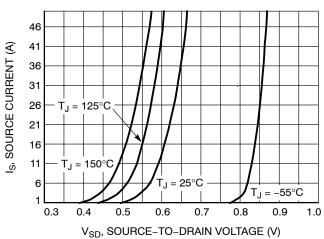


Figure 10. Diode Forward Voltage vs. Current

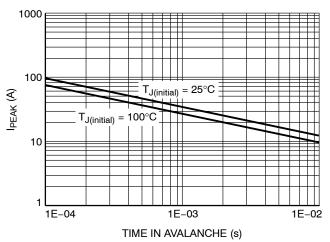


Figure 12. I<sub>PEAK</sub> vs. Time in Avalanche

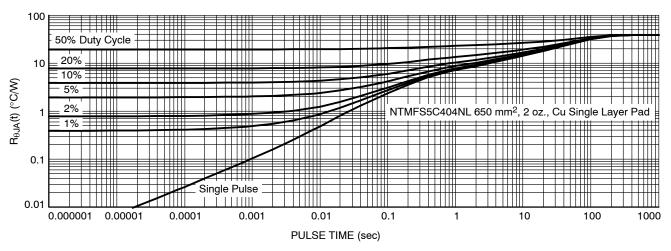


Figure 13. Thermal Characteristics

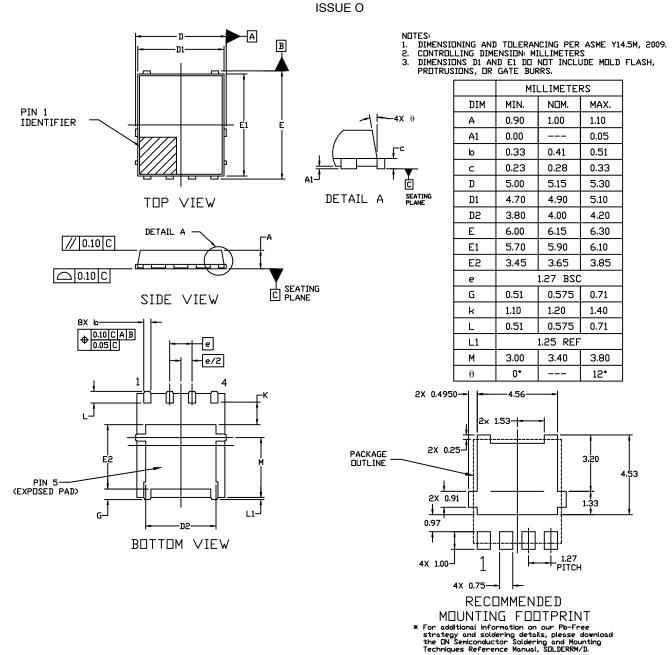
#### **DEVICE ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>
NTMFS5C404NLT1G	5C404L	DFN5 (Pb-Free)	1500 / Tape & Reel
NTMFS5C404NLT3G	5C404L	DFN5 (Pb-Free)	5000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

# **DFN5 5x6, 1.27P (SO-8FL)** CASE 506EZ



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